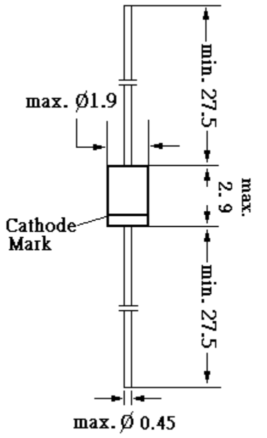
1N4148M

SILICON EPITAXIAL PLANAR DIODE
Fast switching diode



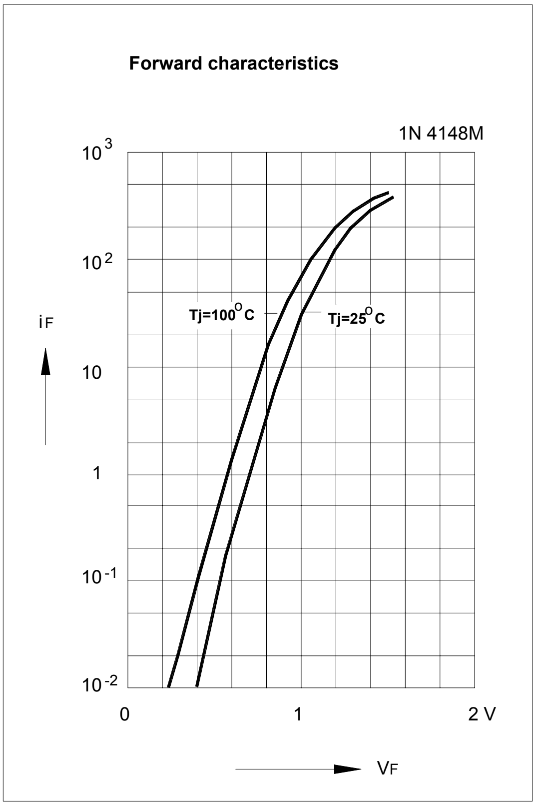
Glass case JEDEC DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^oC$)

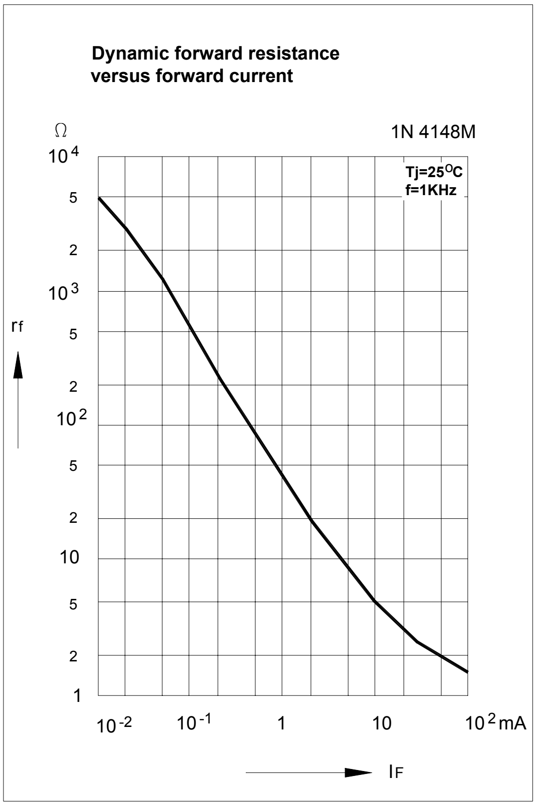
	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Peak Reverse Voltage	V_{RM}	60	V
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb} = 25^oC$ and f/50 H_Z	I_O	130[1]	mA
Surge Forward Current at t<1s and $T_j = 25^oC$	I_{FSM}	500	mA
Power Dissipation	P_{tot}	400[1]	mW
Junction Temperature	T_j	200	^OC
Storage Temperature Range	T_S	-65 to +200	^OC
[1] Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.			

Characteristics at $T_j = 25^oC$

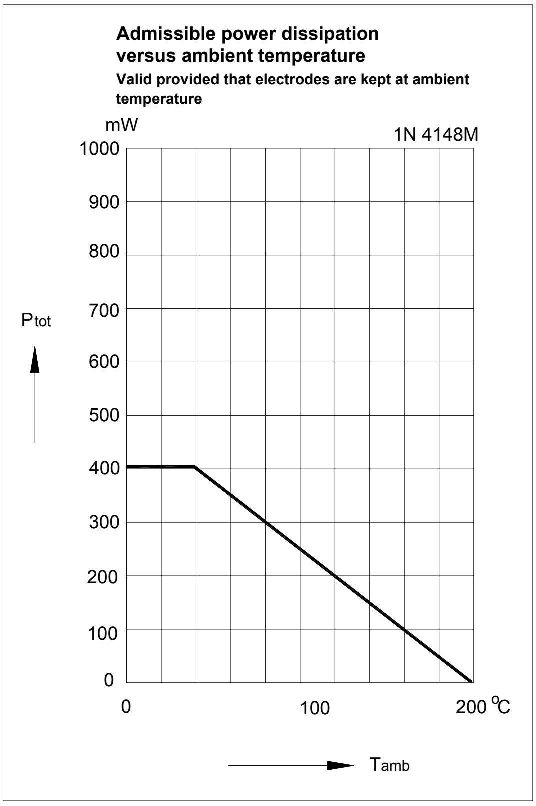
	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100mA$	V_F	-	-	1.1	V
Leakage Current at $V_R = 50V$	I_R	-	-	0.5	µA
Reverse Breakdown Voltage tested with 100µA Pulses	$V_{(BR)R}$	60	-	-	V
Capacitance at $V_F = V_R = 0$	C_{tot}	-	-	3	pF
Reverse Recovery Time from $I_F = 10mA$ to $I_R = 1mA$, $V_R = 6V$, $R_L = 100\Omega$	t_{rr}	-	-	4	ns
[1] Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.					



Forward characteristics

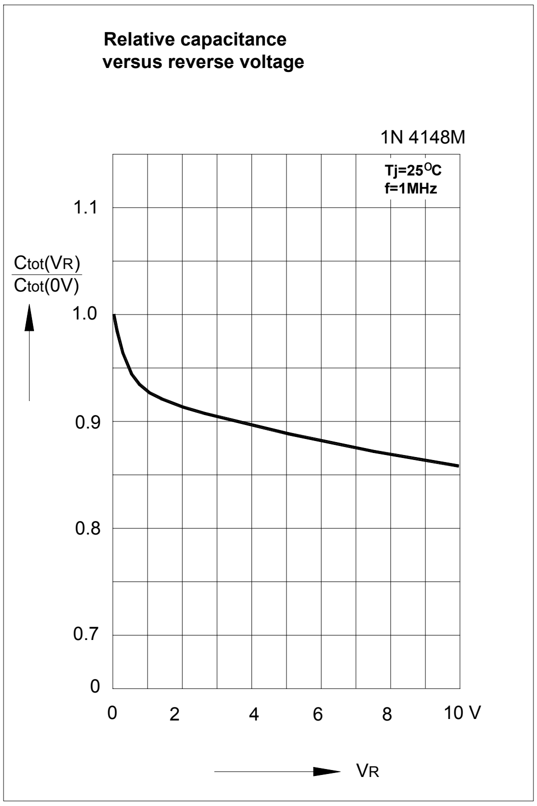


Dynamic forward resistance versus forward current



Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature



Relative capacitance versus reverse voltage